

FDP8874

N-Channel PowerTrench® MOSFET 30V, 114A, 5.3mΩ

General Description

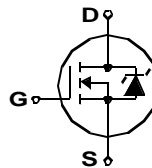
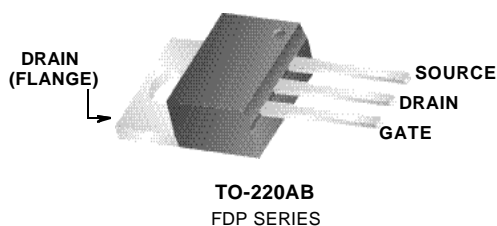
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{DS(ON)}$ and fast switching speed.

Features

- $r_{DS(ON)} = 5.3m\Omega$, $V_{GS} = 10V$, $I_D = 40A$
- $r_{DS(ON)} = 6.6m\Omega$, $V_{GS} = 4.5V$, $I_D = 40A$
- High performance trench technology for extremely low $r_{DS(ON)}$
- Low gate charge
- High power and current handling capability

Applications

- DC/DC converters



MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	± 20	V
I_D	Drain Current		
	Continuous ($T_C = 25^\circ C$, $V_{GS} = 10V$) (Note 1)	114	A
	Continuous ($T_C = 25^\circ C$, $V_{GS} = 4.5V$) (Note 1)	102	A
	Continuous ($T_{amb} = 25^\circ C$, $V_{GS} = 10V$, with $R_{\theta JA} = 62^\circ C/W$)	16	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 2)	105	mJ
P_D	Power dissipation	110	W
	Derate above $25^\circ C$	0.73	W/ $^\circ C$
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	$^\circ C$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case TO-220	1.36	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-220 (Note 3)	62	$^\circ C/W$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP8874	FDP8874	TO-220AB	Tube	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

$B_{V_{DS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$ $V_{GS} = 0\text{V}$	-	-	1	μA
		$T_C = 150^\circ\text{C}$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	1.2	-	2.5	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 40\text{A}, V_{GS} = 10\text{V}$	-	0.0036	0.0053	Ω
		$I_D = 40\text{A}, V_{GS} = 4.5\text{V}$	-	0.0045	0.0066	
		$I_D = 40\text{A}, V_{GS} = 10\text{V},$ $T_J = 175^\circ\text{C}$	-	0.0062	0.0090	

Dynamic Characteristics

C_{ISS}	Input Capacitance	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$	-	3130	-	pF
C_{OSS}	Output Capacitance		-	590	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	345	-	pF
R_G	Gate Resistance	$V_{GS} = 0.5\text{V}, f = 1\text{MHz}$	-	1.9	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$	-	56	72	nC
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0\text{V to } 5\text{V}$	-	30	38	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V to } 1\text{V}$	-	3.0	4.0	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DD} = 15\text{V}$ $I_D = 40\text{A}$ $I_g = 1.0\text{mA}$	-	9.0	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	6.0	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	11	-	nC

Switching Characteristics ($V_{GS} = 10\text{V}$)

t_{ON}	Turn-On Time	$V_{DD} = 15\text{V}, I_D = 40\text{A}$ $V_{GS} = 4.5\text{V}, R_{GS} = 4.7\Omega$	-	-	207	ns
$t_{d(ON)}$	Turn-On Delay Time		-	10	-	ns
t_r	Rise Time		-	128	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	44	-	ns
t_f	Fall Time		-	31	-	ns
t_{OFF}	Turn-Off Time		-	-	112	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 40\text{A}$	-	-	1.25	V
		$I_{SD} = 20\text{A}$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 40\text{A}, dl_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	32	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 40\text{A}, dl_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	18	nC

Notes:

- 1: Package current limitation is 80A.
- 2: Starting $T_J = 25^\circ\text{C}$, $L = 51\mu\text{H}$, $I_{AS} = 64\text{A}$, $V_{DD} = 27\text{V}$, $V_{GS} = 10\text{V}$.
- 3: Pulse width = 100s.

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

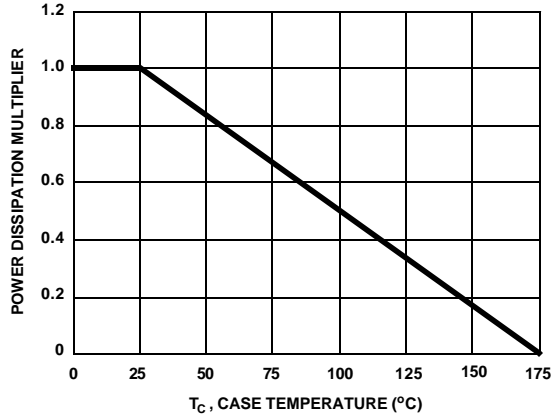


Figure 1. Normalized Power Dissipation vs Case Temperature

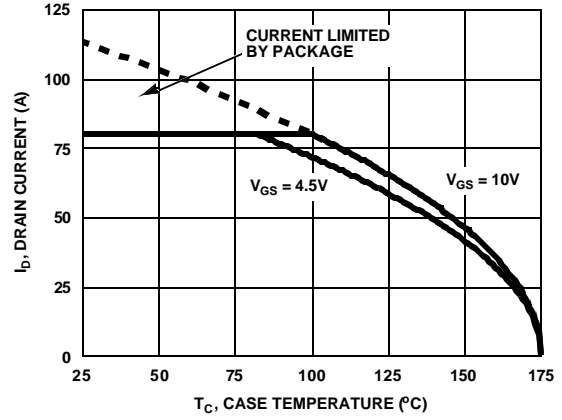


Figure 2. Maximum Continuous Drain Current vs Case Temperature

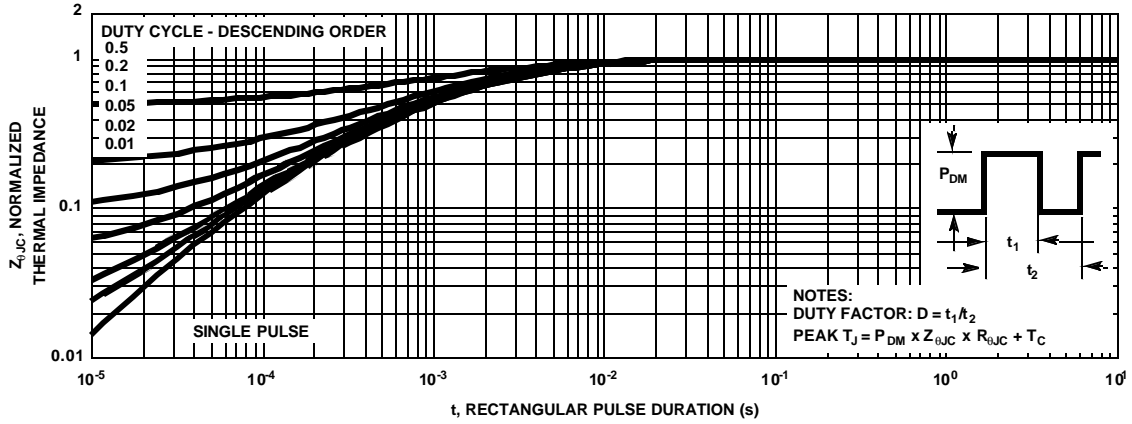


Figure 3. Normalized Maximum Transient Thermal Impedance

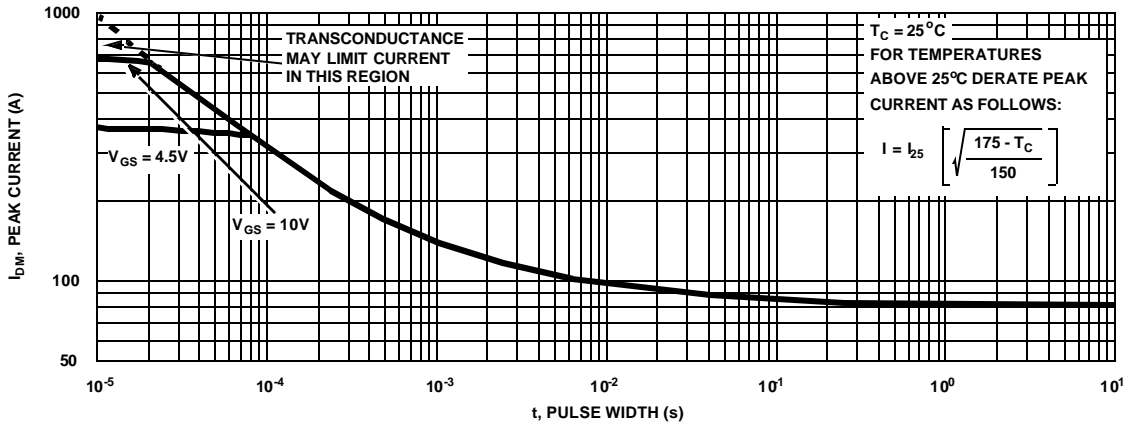


Figure 4. Peak Current Capability

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

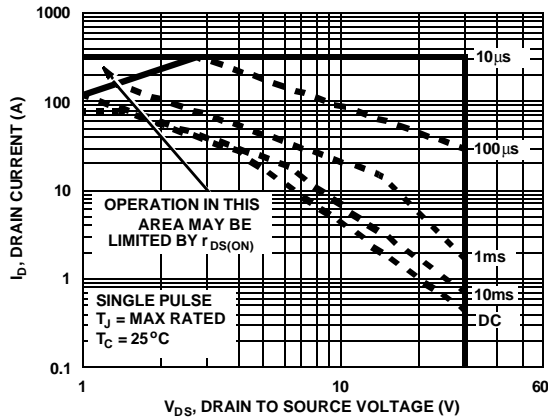
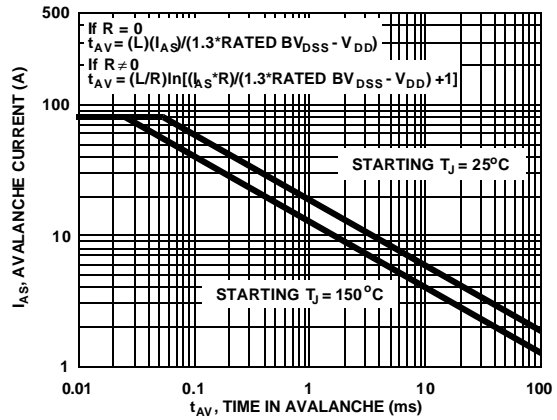


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515
Figure 6. Unclamped Inductive Switching Capability

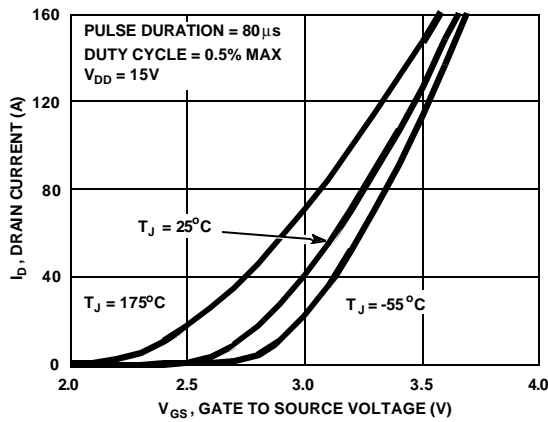


Figure 7. Transfer Characteristics

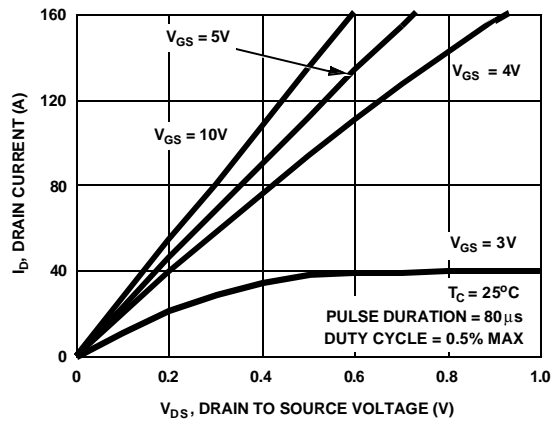


Figure 8. Saturation Characteristics

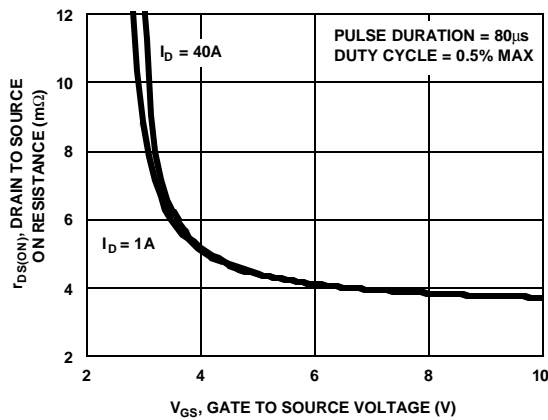


Figure 9. Drain to Source On Resistance vs Gate Voltage and Drain Current

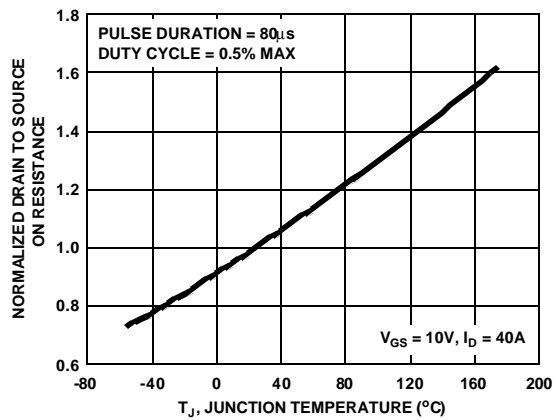


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

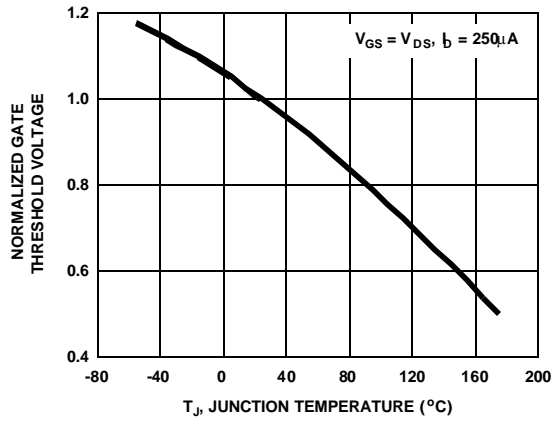


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

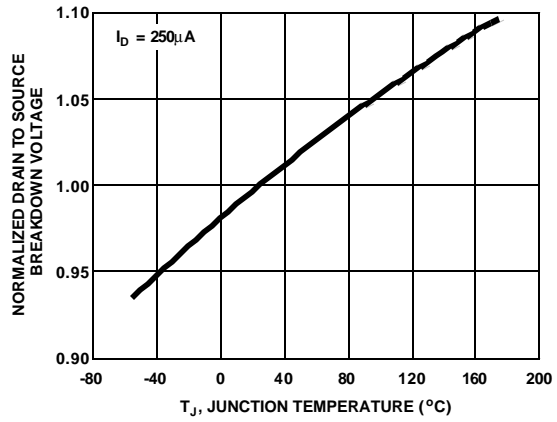


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

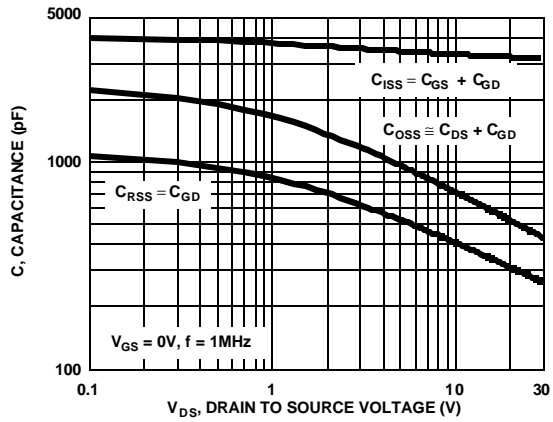


Figure 13. Capacitance vs Drain to Source Voltage

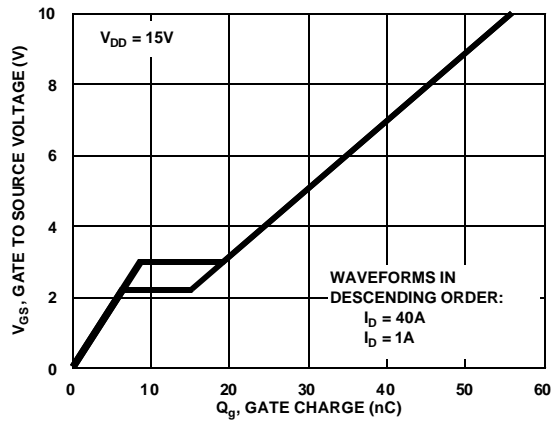


Figure 14. Gate Charge Waveforms for Constant Gate Current

Test Circuits and Waveforms

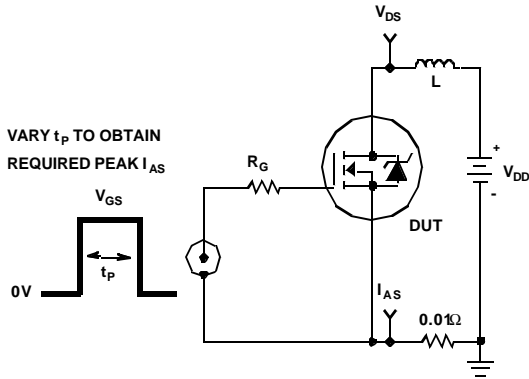


Figure 15. Unclamped Energy Test Circuit

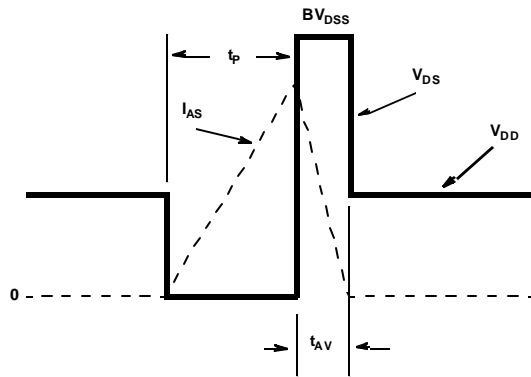


Figure 16. Unclamped Energy Waveforms

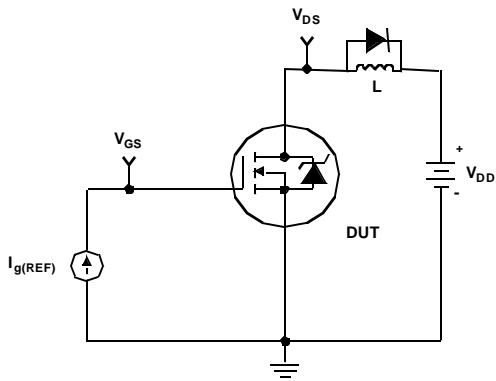


Figure 17. Gate Charge Test Circuit

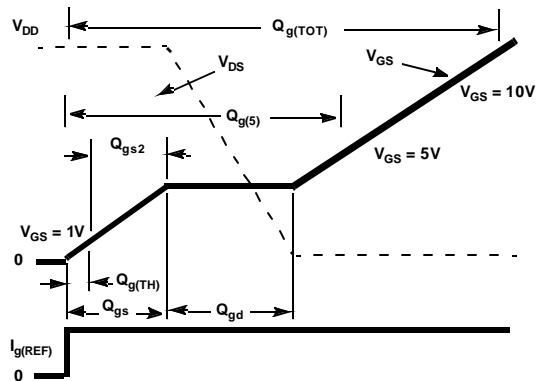


Figure 18. Gate Charge Waveforms

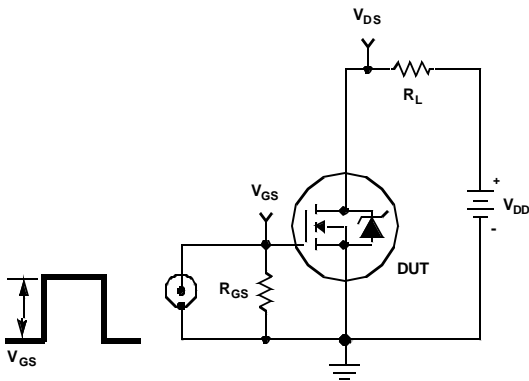


Figure 19. Switching Time Test Circuit

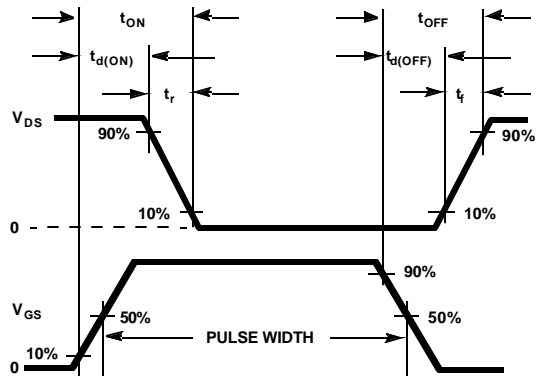


Figure 20. Switching Time Waveforms

SABER Electrical Model

rev May 2004
 template FDP8874 n2,n1,n3
 electrical n2,n1,n3

```

{
var i iscl
dp..model dbodymod = (isl=4.1e-12,ikf=10,ni=1.01,rs=2e-3,trs1=8e-4,trs2=2e-7,cjo=1.22e-9,m=0.57,tt=3e-12,xti=3)
dp..model dbreakmod = (rs=8e-2,trs1=1e-3,trs2=-8.9e-6)
dp..model dplcapmod = (cjo=1.12e-9,isl=10e-30,ni=10,m=0.42)
m..model mmedmod = (type=_n,vto=2,kp=9,is=1e-30,tox=1)
m..model mstrongmod = (type=_n,vto=2.5,kp=390,is=1e-30,tox=1)
m..model mweakmod = (type=_n,vto=1.72,kp=0.05,is=1e-30,tox=1,rs=0.1)
sw_vcsp..model s1amod = (ron=1e-5,roff=0.1,von=-4,voff=-3)
sw_vcsp..model s1bmod = (ron=1e-5,roff=0.1,von=-3,voff=-4)
sw_vcsp..model s2amod = (ron=1e-5,roff=0.1,von=-2,voff=-0.5)
sw_vcsp..model s2bmod = (ron=1e-5,roff=0.1,von=-0.5,voff=-2)
c.ca n12 n8 = 2.3e-9
c.cb n15 n14 = 2.25e-9
c.cin n6 n8 = 2.9e-9
    
```

```

dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod
    
```

```

spe.ebreak n11 n7 n17 n18 = 33.3
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evthres n6 n21 n19 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1
    
```

```
i.it n8 n17 = 1
```

```

l.lgate n1 n9 = 8.5e-9
l.ldrain n2 n5 = 1.0e-9
l.lsource n3 n7 = 2.7e-9
    
```

```

res.rlgate n1 n9 = 85
res.rldrain n2 n5 = 10
res.rlsource n3 n7 = 27
    
```

```

m.mmed n16 n6 n8 n8 = model=mmedmod, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, l=1u, w=1u
    
```

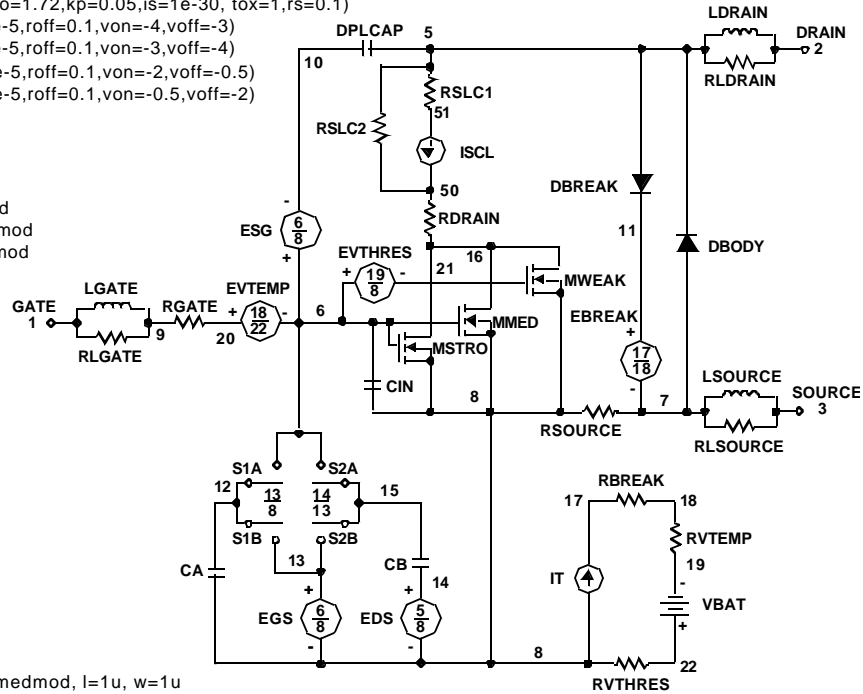
```

res.rbreak n17 n18 = 1, tc1=8.3e-4,tc2=-8e-7
res.rdrain n50 n16 = 1.7e-3, tc1=7e-3,tc2=3.8e-6
res.rgate n9 n20 = 1.9
res.rslc1 n5 n51 = 1e-6, tc1=1e-4,tc2=1e-6
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7 = 1.7e-3, tc1=1e-4,tc2=2.5e-6
res.rvthres n22 n8 = 1, tc1=-2.4e-3,tc2=-8e-6
res.rvtemp n18 n19 = 1, tc1=-1.8e-3,tc2=2e-7
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod
    
```

```
v.vbat n22 n19 = dc=1
```

```

equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51))*1e6/500))** 10))
}
}
    
```



PSPICE Thermal Model

REV 23 May 2004

FDP8874T

CTHERM1 TH 6 1.9e-3
 CTHERM2 6 5 2.8e-3
 CTHERM3 5 4 3.5e-3
 CTHERM4 4 3 3.6e-3
 CTHERM5 3 2 4.0e-3
 CTHERM6 2 TL 1.6e-2

RTHERM1 TH 6 3.8e-2
 RTHERM2 6 5 5.0e-2
 RTHERM3 5 4 1.0e-1
 RTHERM4 4 3 1.8e-1
 RTHERM5 3 2 3.5e-1
 RTHERM6 2 TL 3.7e-1

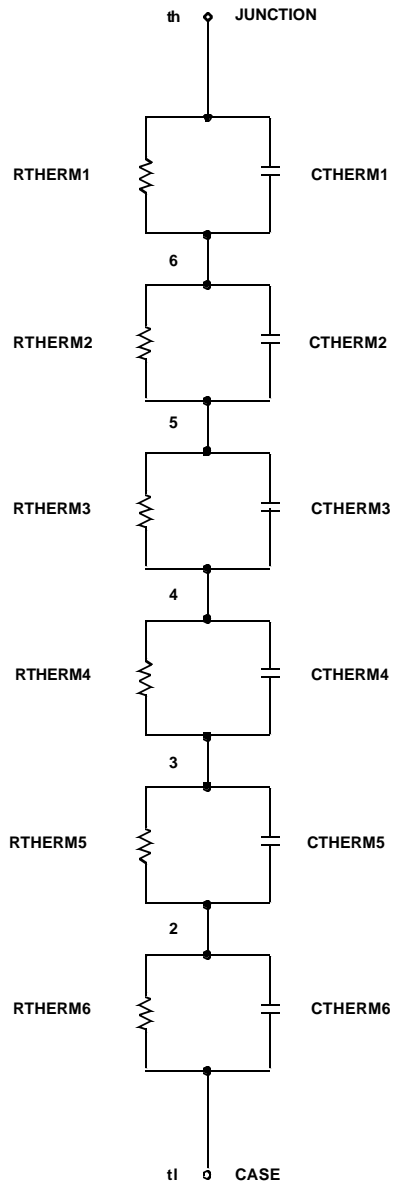
SABER Thermal Model

SABER thermal model FDP8874T

template thermal_model th tl
 thermal_c th, tl

```
{
ctherm.ctherm1 th 6 =1.9e-3
ctherm.ctherm2 6 5 =2.8e-3
ctherm.ctherm3 5 4 =3.5e-3
ctherm.ctherm4 4 3 =3.6e-3
ctherm.ctherm5 3 2 =4.0e-3
ctherm.ctherm6 2 tl =1.6e-2
```

```
rtherm.rtherm1 th 6 =3.8e-2
rtherm.rtherm2 6 5 =5.0e-2
rtherm.rtherm3 5 4 =1.0e-1
rtherm.rtherm4 4 3 =1.8e-1
rtherm.rtherm5 3 2 =3.5e-1
rtherm.rtherm6 2 tl =3.7e-1
}
```



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CoolFET™	FRFET™	MicroFET™	PowerTrench®	SuperSOT™-6
CROSSVOLT™	GlobalOptoisolator™	MicroPak™	QFET®	SuperSOT™-8
DOMET™	GTO™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	HiSeC™	MSX™	QT Optoelectronics™	TinyLogic®
E ² CMOS™	ꝑC™	MSXPro™	Quiet Series™	TINYOPTO™
EnSigna™	i-Lo™	OCX™	RapidConfigure™	TruTranslation™
FACT™	ImpliedDisconnect™	OCXPro™	RapidConnect™	UHC™
FACT Quiet Series™		OPTOLOGIC®	µSerDes™	UltraFET®
Across the board. Around the world.™		OPTOPLANAR™	SILENT SWITCHER®	VCX™
The Power Franchise®		PACMAN™	SMART START™	
Programmable Active Droop™		POP™	SPM™	

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